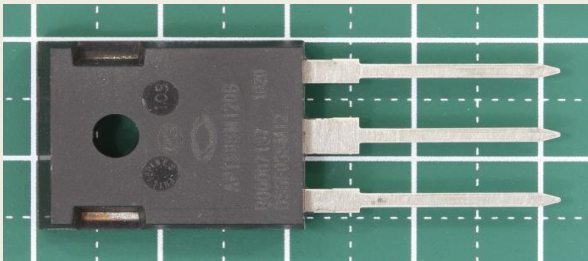


Microsemi APT80SM120B 1200V SiC MOSFET ANALYSIS REPORT

November 2017. LTEC Corporation released a detailed structure and process analysis report of this 1200V silicon carbide MOSFET of Microsemi. This device is the 1st 1200V product from



Package



SiC die

Device features

- Max. operating voltage: 1200V, rated DC Drain current $I_D=80A$ at $T_j=25^\circ C$
- ON-resistance, $R_{ON} \times A = 1,076m\Omega \times mm^2$
- Double metal layer at Source PADs and Gate PADs is used in order to maximize the package density

The report has two individually purchasable sections: an 73-page Structure Analysis, and a 23-page Process Analysis section. The Structure Analysis section reveals the physical construction of the device, including EDX materials analysis, and many other fine details. The Process Analysis section includes manufacturing process flow, the estimated number of photomasking steps, and the impurity concentration of the epitaxial layer.

Structure analysis report: \$4,000

Process analysis report: \$4,000

Note: The listed report price may not be accurate as it decreases over time.

Please contact us for current report pricing : info@ltecusa.com

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